

RADIATION TEST SUMMARY

PART TYPE: IRF9140

DESCRIPTION: P-CHANNEL POWER MOS FET

REPORT NO: RD148

PARAMETERS PLOTTED:

$V_{GS(TH)}$

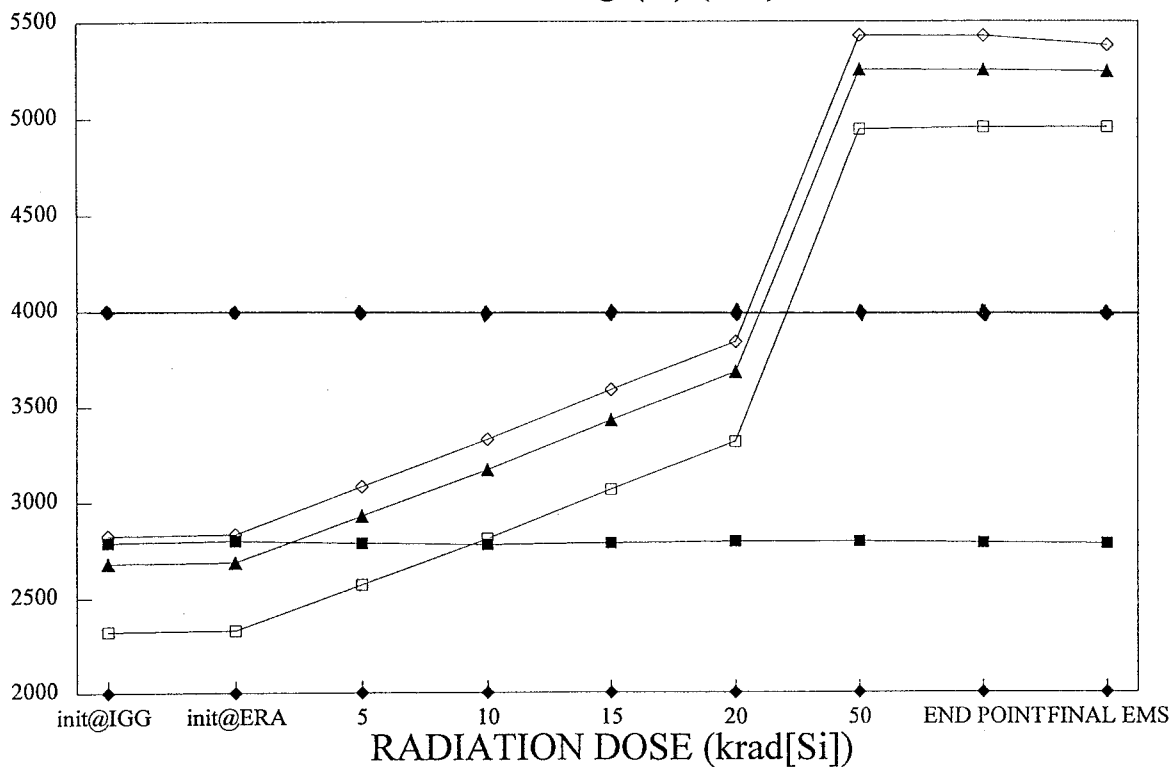
$r_{DS(ON)}$

NOTE

The results for I_{GSS} , $V_{(BR)DSS}$ and I_{DSS} showed no significant change and hence these plots were not considered necessary.

RADIATION RESULTS FOR IRF9140

Plot for Vgs(th) (mV)



Control
 Limit
 Mean
 Min.
 Max.

>2.0V<4.0V

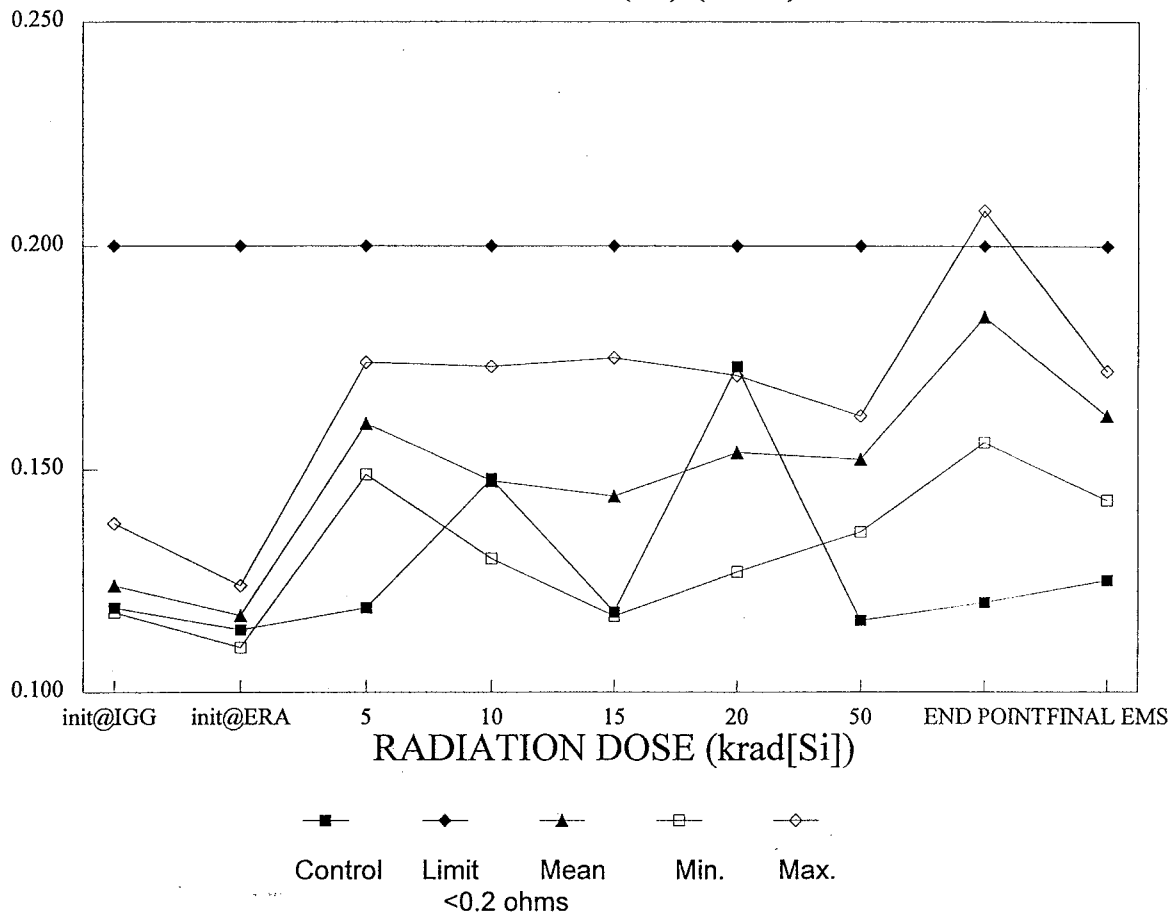
DOSE krad	Mean-value	S.D.	Max.value	Min.value
INIT @ IGG	2681.3	207.6	2826.6	2322.8
0	2689.0	208.1	2834.9	2329.6
5	2928.6	208.7	3079.6	2569.1
10	3168.8	209.5	3326.3	2809.6
15	3427.2	212.3	3584.4	3064.6
20	3676.3	211.8	3833.8	3315.3
50	5249.1	194.8	5426.8	4939.5
END POINT	5248.4	188.1	5426.4	4949.3
FINAL EMS	5240.0	171.5	5376.9	4951.4

Lot size for statistics : 4 devices

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RADIATION RESULTS FOR IRF9140

Plot for rDS(on) (ohms)



DOSE krad	Mean-value	S.D.	Max.value	Min.value
INIT @ IGG	0.124	0.008	0.138	0.118
0.000	0.117	0.005	0.124	0.110
5.000	0.160	0.011	0.174	0.149
10.000	0.148	0.017	0.173	0.130
15.000	0.144	0.023	0.175	0.117
20.000	0.154	0.017	0.171	0.127
50.000	0.152	0.010	0.162	0.136
END POINT	0.184	0.020	0.208	0.156
FINAL EMS	0.162	0.011	0.172	0.143

Lot size for statistics : 4 devices

RD 148 Date Code 9518B